

Please add the following new claims:

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9. (New) A bidirectional semiconductor component, comprising:
a substrate including a drain region; and
two symmetrical MOS transistor structures integrated laterally in the substrate and connected to each other antiserially, a drain terminal of each of the two symmetrical MOS transistor structures being connected to one another, wherein:
a zone having a conductivity that is the same as a conductivity of the drain region and having a doping that is higher than a doping of the drain region is situated upstream from a pn junction of one of the two symmetrical MOS transistor structures in a junction area with the drain region.
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10. (New) The bidirectional semiconductor component according to claim 9, wherein:
the drain region and the zone are n-doped.
11. (New) The bidirectional semiconductor component according to claim 9, further comprising:
a layer on which the drain region is situated and having a doping that is opposite that of the conductivity of the drain region.
12. (New) The bidirectional semiconductor component according to claim 11, wherein:
the layer includes a plurality of partial layers having stepped doping.
13. (New) A method of using a bidirectional semiconductor component, comprising the step of:
using the bidirectional semiconductor component as a short-circuit switch to short circuit a primary winding of an ignition coil in an ignition power module of an ignition system of an internal combustion engine, wherein the bidirectional semiconductor component includes:
a substrate including a drain region; and

two symmetrical MOS transistor structures integrated laterally in the substrate and connected to each other antiseriably, a drain terminal of each of the two symmetrical MOS transistor structures being connected to one another wherein:
 a zone having a conductivity that is the same as a conductivity of the drain region and having a doping that is higher than a doping of the drain region is situated upstream from a pn junction of one of the two symmetrical MOS transistor structures in a junction area with the drain region.

14. (New) The method according to claim 13, further comprising the steps of:

performing a time-staggered activation of gate terminals of the two symmetrical MOS transistor structures in a time-staggered manner; and
 activating at a later time one of the two symmetrical MOS transistor structures that blocks a higher voltage.

15. (New) The ignition system according to claim 14, wherein:
 the time-staggered activation is performed by interconnecting a capacitor.
16. (New) The ignition system according to claim 14, wherein:
 the time-staggered activation is performed by a time control.

Remarks

This Preliminary Amendment cancels original claims 1-8, without prejudice in the underlying PCT Application No. PCT/DE00/02061. The Preliminary Amendment also adds new claims 9-16. The new claims conform the claims to U.S. Patent and Trademark Office rules and do not add new matter to the application.

In accordance with 37 C.F.R. § 1.121(b)(3), the Substitute Specification (including the Abstract, but without the claims) contains no new matter. The amendments reflected in the Substitute Specification (including Abstract) are to conform the Specification and Abstract to U.S. Patent and Trademark Office rules or to correct informalities. As required by 37 C.F.R. § 1.121(b)(3)(iii) and § 1.125(b)(2), a Marked Up Version Of The Substitute Specification comparing the Specification of record and the